

The Second Korea-Japan Workshop on Nanomaterials for IT''

Co-Sponsors;

Brain-Korea, Sung-King-Kang University,
Nanomaterials Innovation G-COE, Tokyo Institute of Technology,

Venue:

Song-King-Kang University, Sewan, Korea

Date:

December 27,2007

Oral Presentation at conference room (83188) of the Second Research Building

10:00 ~ 10:15: Opening address & introduction of advanced material BK21

Prof. Yeom Geun-Young in SKKU, Korea

10:15 ~ 10:30: Introduction of G-COE Material Innovation, TIT

Prof. Hideo Hosono in TIT, Japan

1st Session

Chairman: Prof. Hyung Koun Cho (SKKU, Korea)

10:30 ~ 10:50: Effect of acetylene partial pressure on height of carbon nanotubes in water
assisted CVD,

S. P. Patole in SKKU, Korea

10:50 ~ 11:10: Growth and characteristics of GaN epilayer on β -Ga₂O₃ substrate by
nitridation ,

H.J. Lee in SKKU, Korea

11:10 ~ 11:30: Control of melt state for pore-free 12CaO•7Al₂O₃ single crystal growth by
floating zone method,

S. G Yoon in TIT, Japan

11:30 ~ 11:50: The enhanced thermal stability and emission features of F⁻ incorporated
12CaO•7Al₂O₃,

J. Li in TIT, Japan

Lunch

2nd Session

Chairman: Dr. Sung-Wng Kim (TIT, Japan)

13:00 ~ 13:20: Characterization of double heterostructure MgZnO/ZnO with low Mg composition,

Y. Y. Kim in SKKU, Korea

13:20 ~ 13:40: Oxygen vacancy clustering in oxygen deficient SrTiO_{3-δ}
: Experimental evidence,

E. Choi in SKKU, Korea

13:40 ~ 14:00: Incorporated anion-induced cage deformation and the anion distribution in the cage in [Ca₂₄Al₂₈O₆₄]⁴⁺•X (X=2O⁻², 4OH⁻¹) crystals,

T. Nomura in TIT, Japan

14:00 ~ 14:20: Ni-based oxyphosphide superconductor, LaNiOP,

T. Watanabe in TIT, Japan

14:30 ~ 15:30: **Coffee Break & poster presentation**

3rd Session

Chairman: Prof. Hoo-Jeong Lee (SKKU, Korea)

15:30 ~ 15:50: Specific contact resistance at interfaces between a-IGZO and various electrodes,

Y. Shimura in TIT, Japan

15:50 ~ 16:10: Fabrication of ScAlMgO₄ single-crystalline thin films by a reactive solid phase epitaxy and its application to lattice-matched buffer layer for ZnO,

T. Katase in TIT, Japan

16:10 ~ 16:30: Morphology and Photoluminescence Properties of Flux additive BaMgAl₁₀O₁₇:Eu²⁺ Phosphor by LPP Method,

A. Dulda in SKKU, Korea

16:30 ~ 16:50: Effects of RF power and post annealing temperature on characteristics of ZnO thin film transistors ,

B. I. Hwang in SKKU, Korea

16:50 ~ 17:10: Reduction Potential of Carbon Nanotubes,

J. H. Lee in SKKU, Korea

17:10 ~ 17:20: **Closing remark**

17:30 ~ : **Dinner Party**